

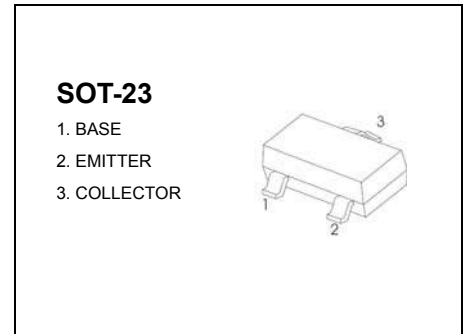
## SOT-23 Plastic-Encapsulate Transistors (NPN)

**S9018**      TRANSISTOR (NPN)

**FEATURES**

- AM/FM Amplifier, Local Oscillator of FM/VHF Tuner
- High Current Gain Bandwidth Product

**MARKING: J8**



**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>c</sub>	Collector Current -Continuous	50	mA
P <sub>c</sub>	Collector Power Dissipation	200	mW
F <sub>&gt;5'</sub>	Thermal Resistance from Junction to Ambient	625	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

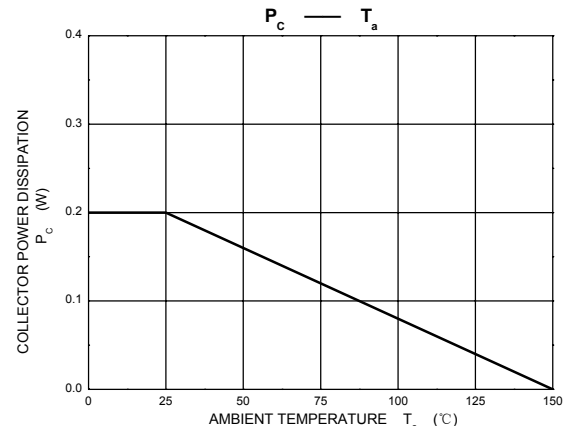
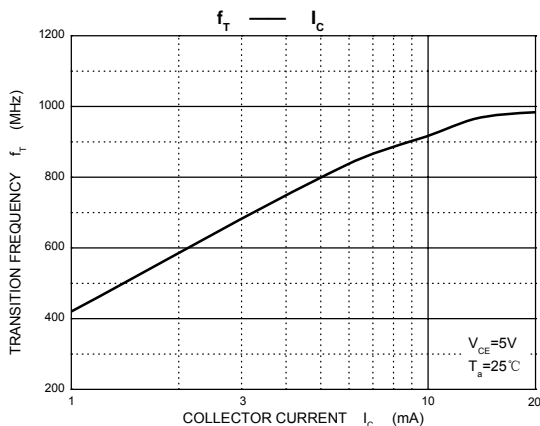
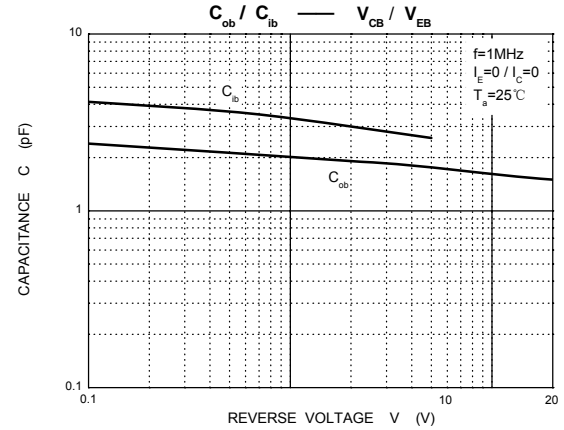
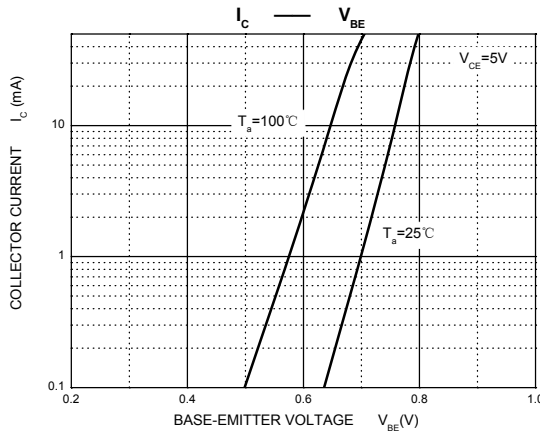
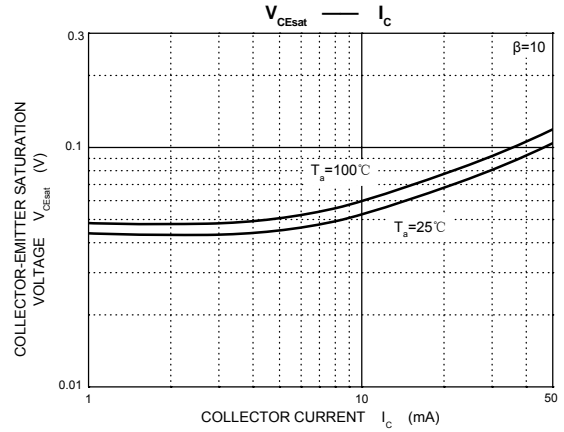
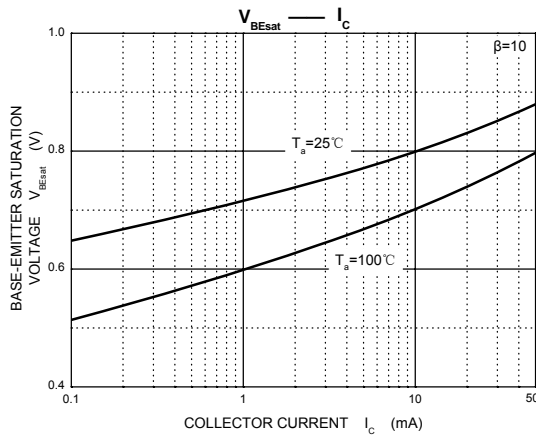
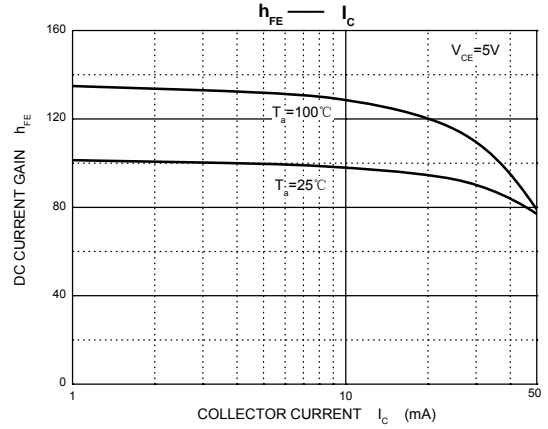
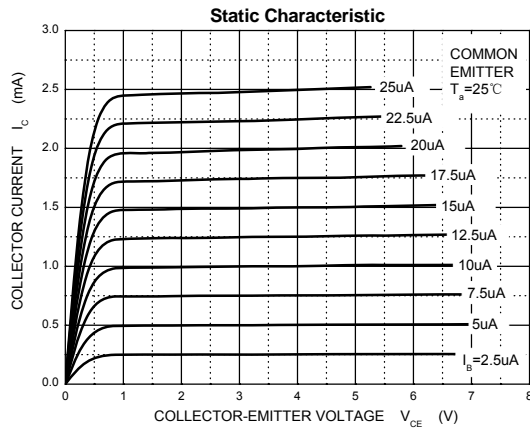
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 100μA, I <sub>E</sub> =0	30			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> =0	15			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =12V, I <sub>E</sub> =0			0.05	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =12V, I <sub>B</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> = 1mA	70		190	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> = 1mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> = 1mA			1.4	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> = 5mA f=400MHz		800		MHz

**CLASSIFICATION OF h<sub>FE</sub>**

Rank	L	H
Range	70-105	105-190

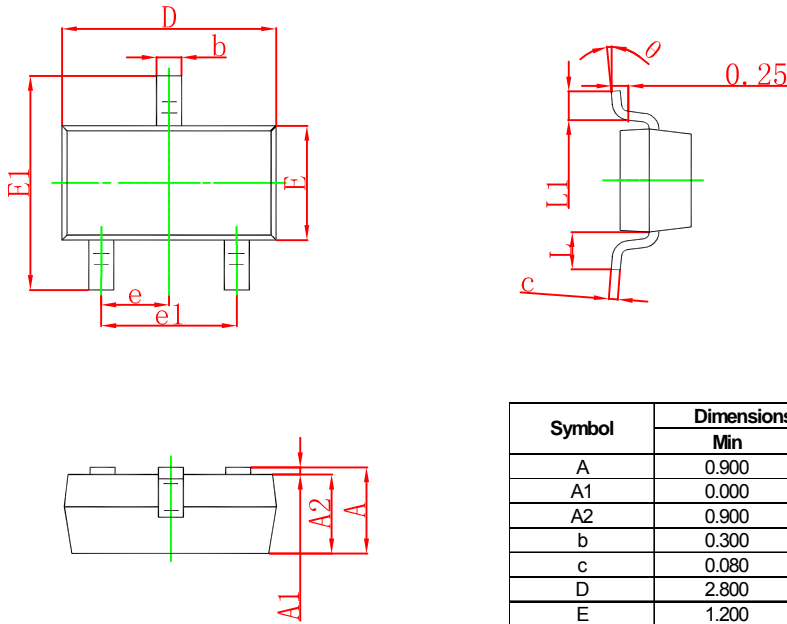
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## Typical Characteristics



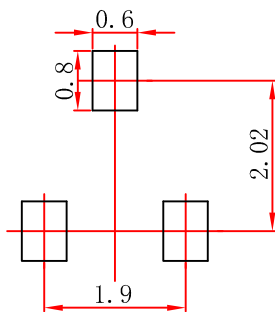
## SOT-23 Plastic-Encapsulate Transistors (NPN)

### SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.